

FIG. 1

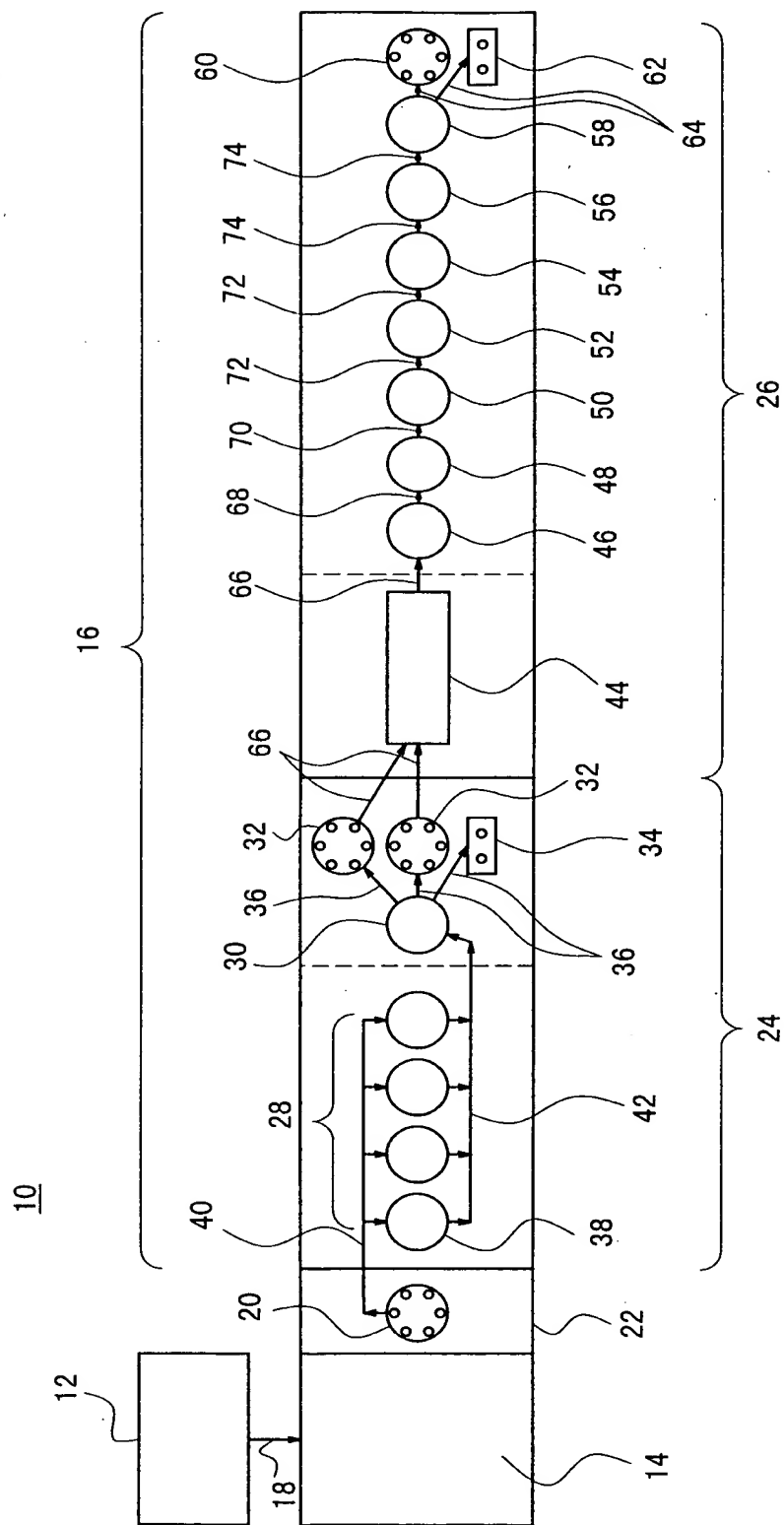
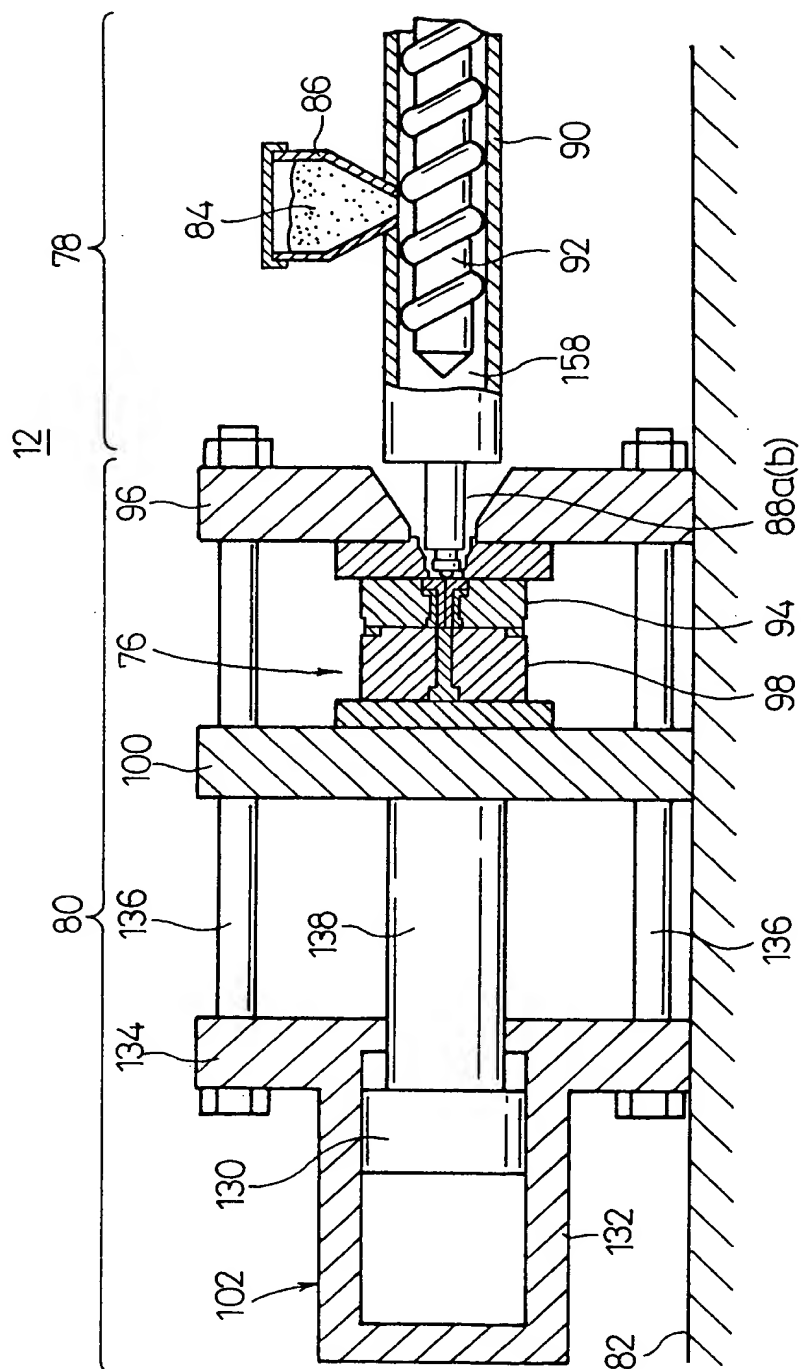
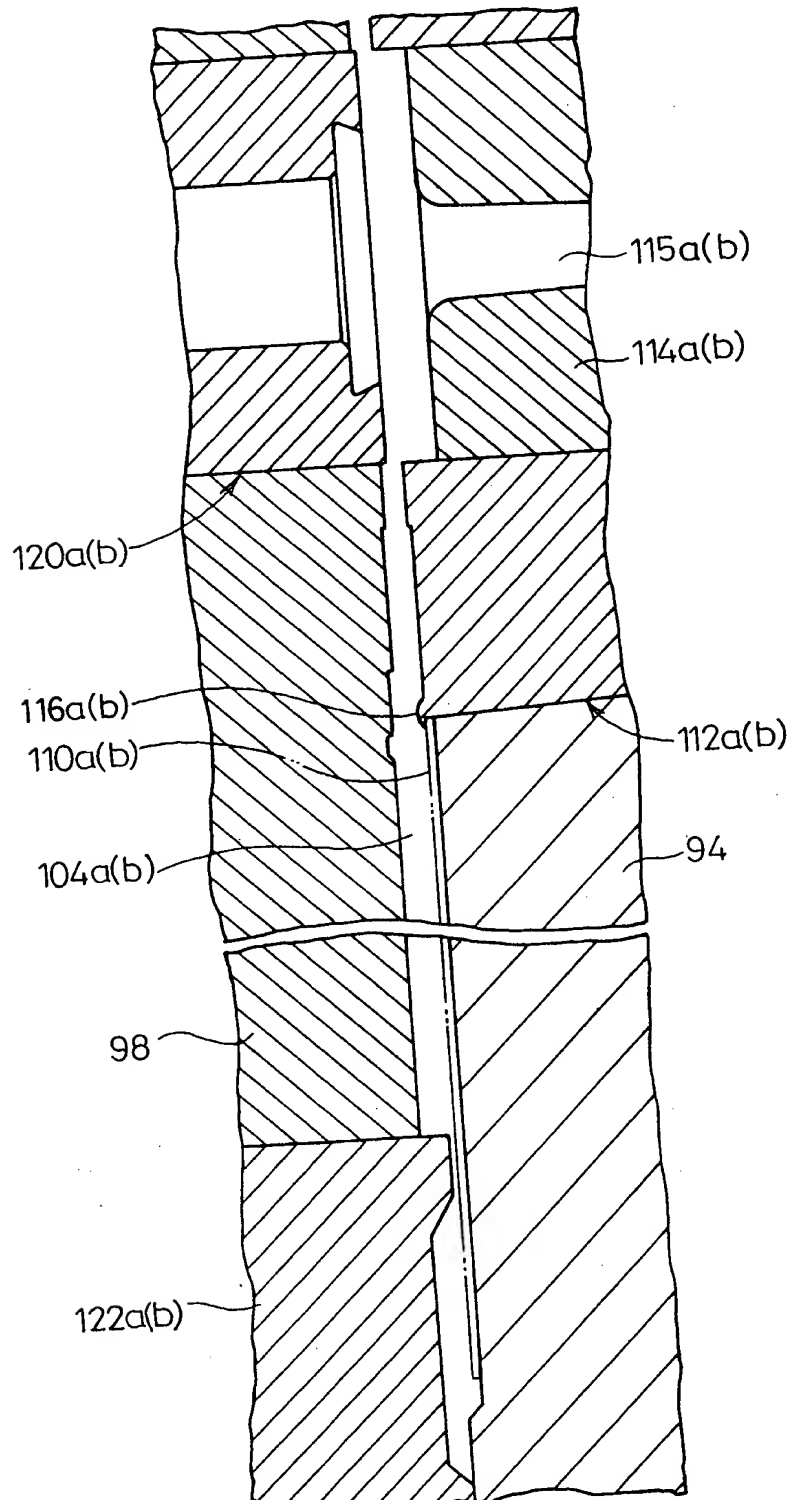


FIG. 2



[illegible]



[illegible]

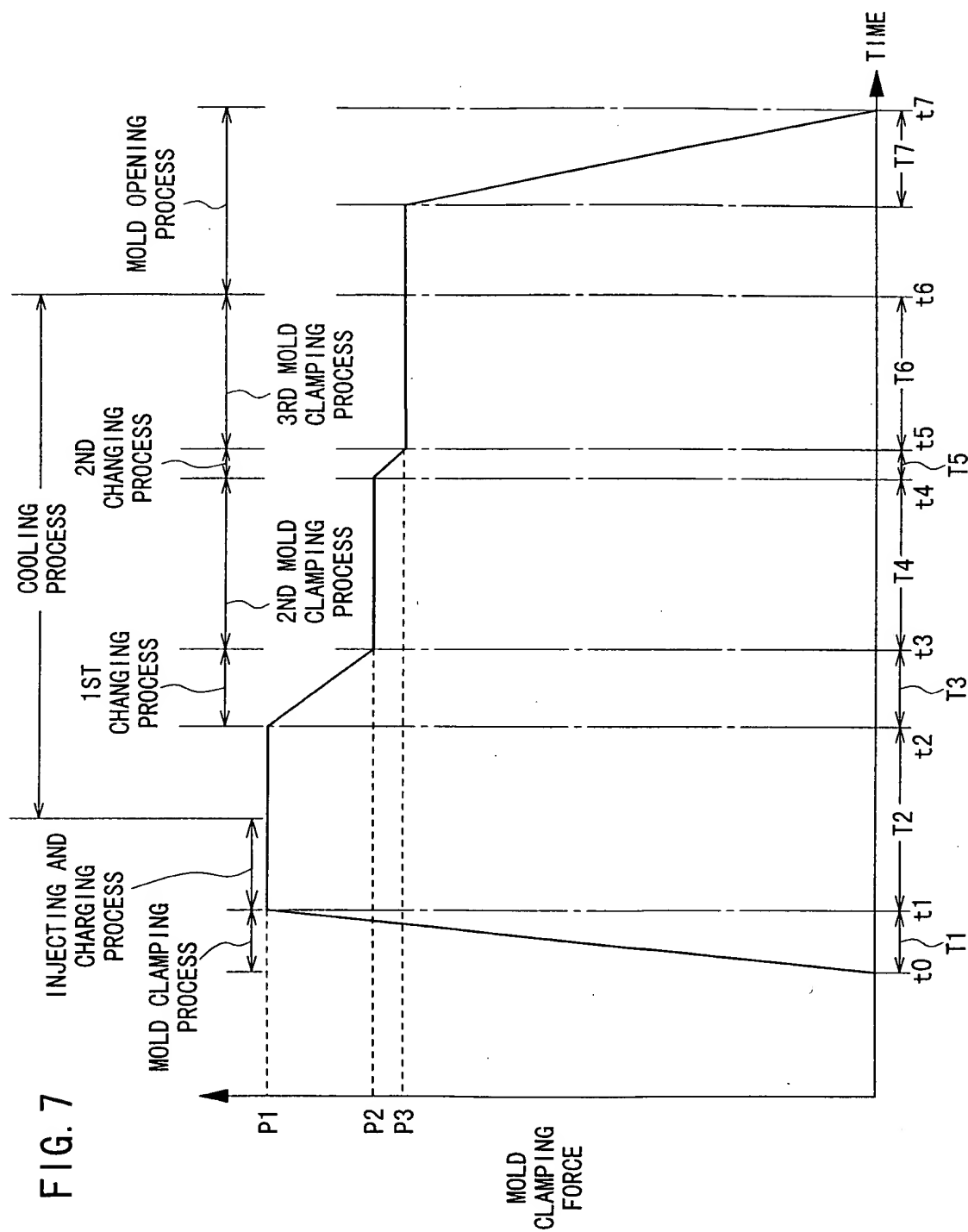


FIG. 8

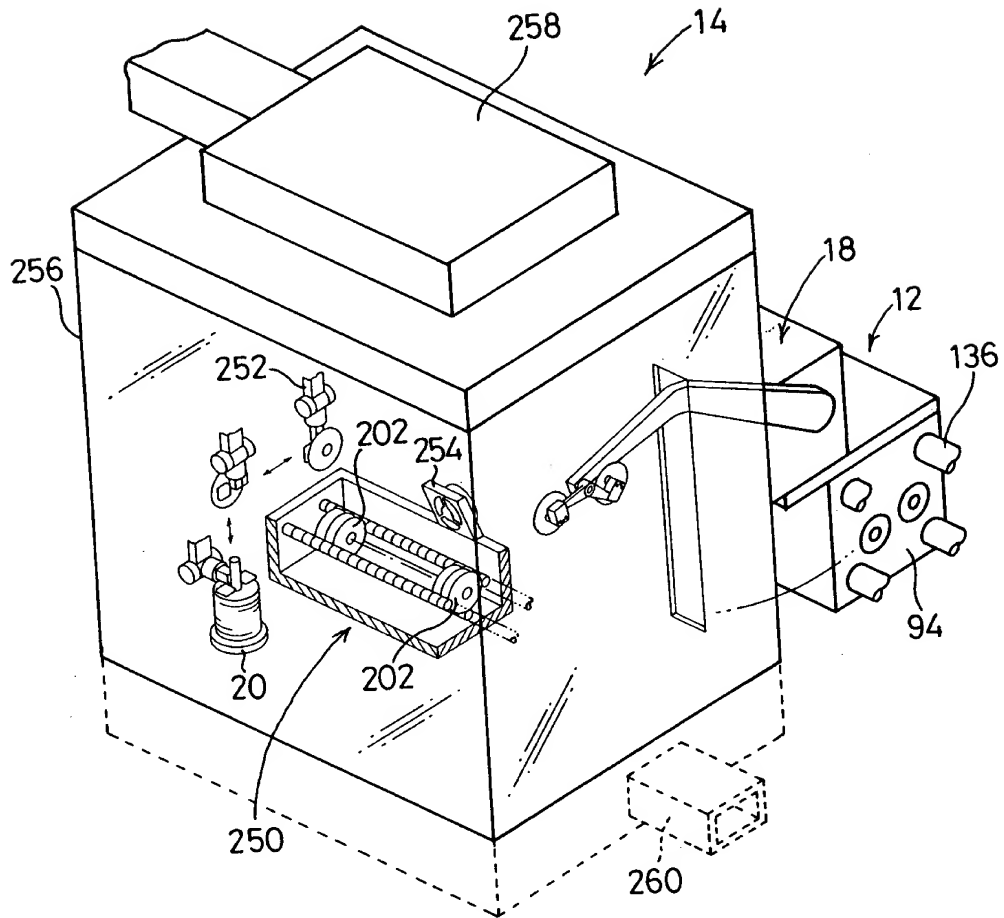


FIG. 10A

FIG. 10A is a cross-sectional view of a substrate 200. The substrate has a series of rectangular protrusions 202 on its top surface. A break symbol is shown in the middle of the substrate.

FIG. 10B

FIG. 10B is a cross-sectional view of a segmented strip assembly. The assembly consists of a series of rectangular segments (200) joined by a continuous layer (202). A top layer (204) is applied over the segments. A break line is shown in the middle of the assembly.

FIG. 10C is a cross-sectional view of a device. It shows a substrate 200 with a top layer 202. A series of rectangular features 204 are formed in the top layer 202, with a gap 206 between them. A curved line 208 is shown above the features 204.

This cross-sectional view shows a substrate 200 with a series of rectangular trenches 202. A layer 204 is deposited within these trenches, and a top layer 206 is formed over the entire structure. A cross-section line 208 is indicated by a curved line passing through the device.

A cross-sectional view of a semiconductor device. It shows a substrate 200 with a series of rectangular protrusions 202 on its top surface. A layer 204 is deposited over these protrusions, forming a continuous film. A layer 208 is then deposited over layer 204. A trench 210 is formed in layer 208, extending through it and into layer 204. A curved line labeled 'D' represents a cross-section of a trench or a defect line passing through the layers.

FIG. 12

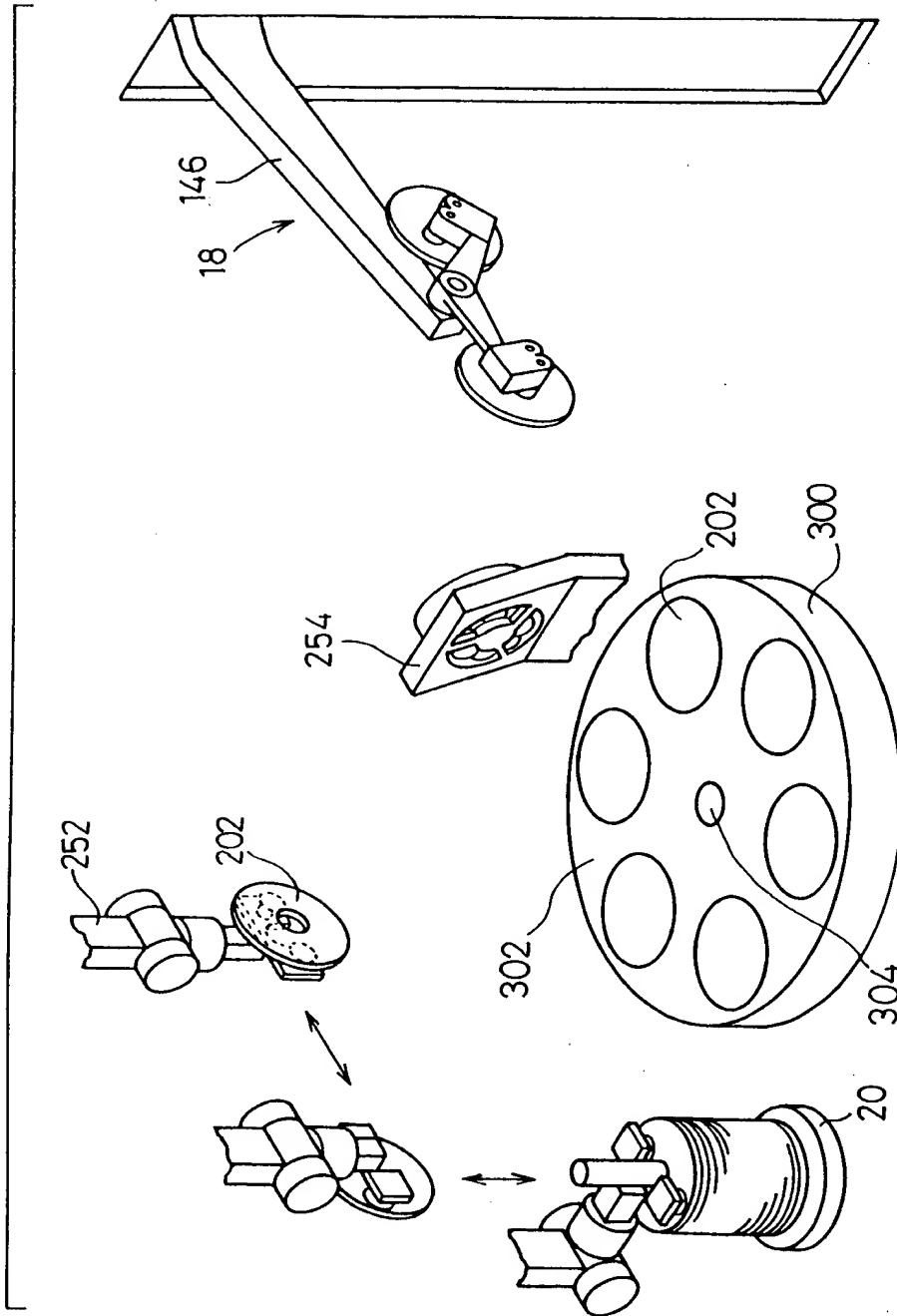


FIG. 13

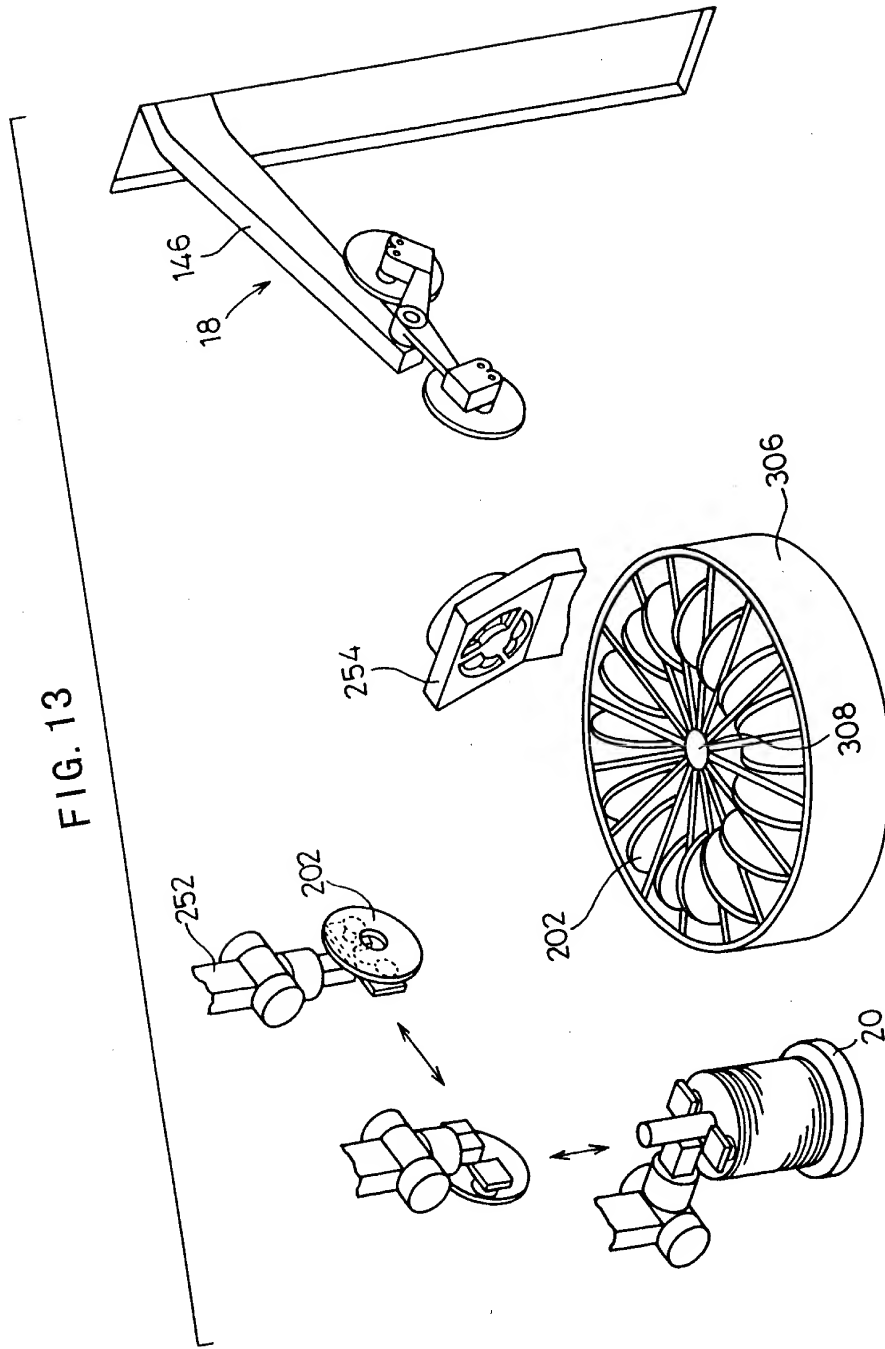


FIG. 14

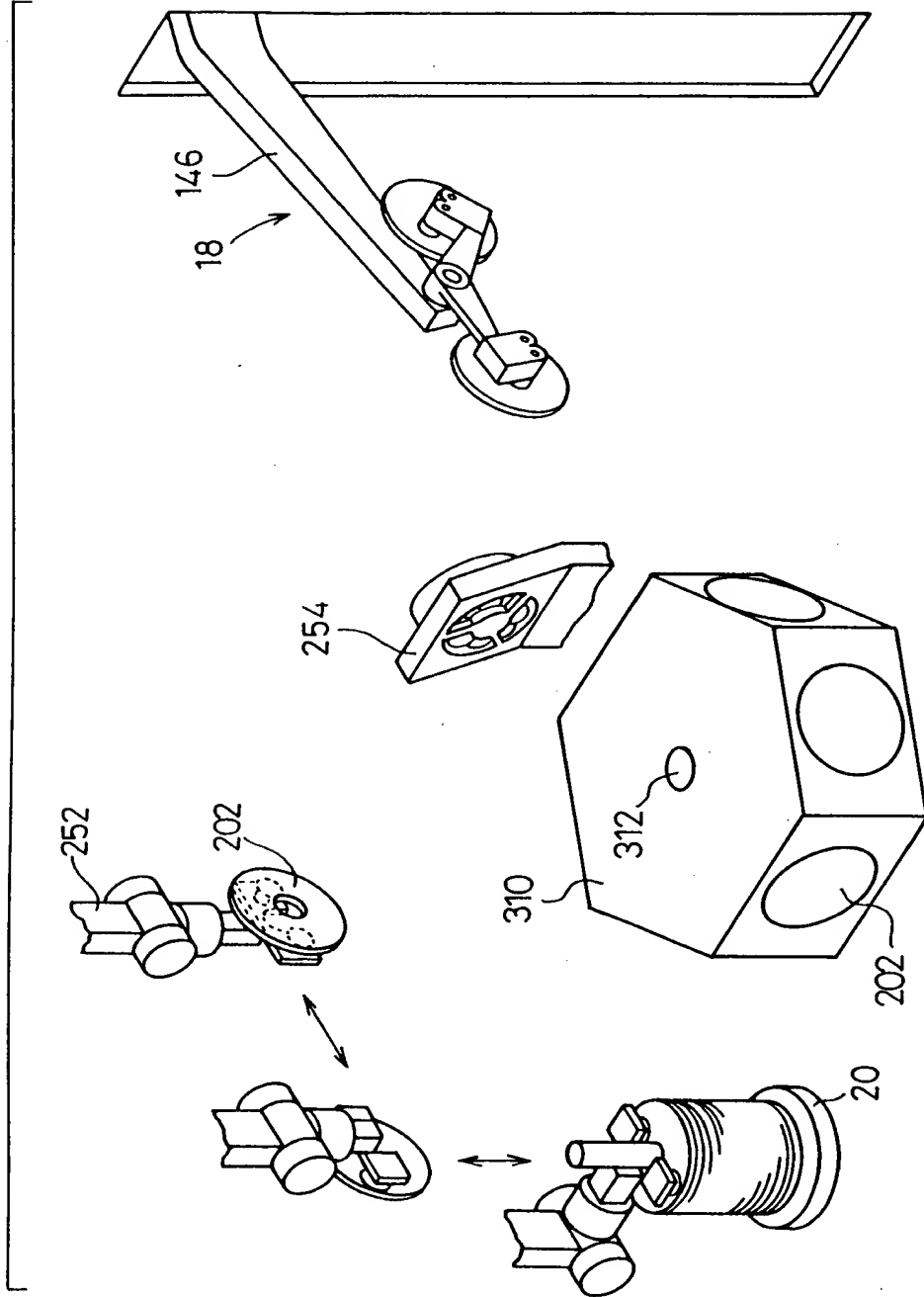


FIG. 15

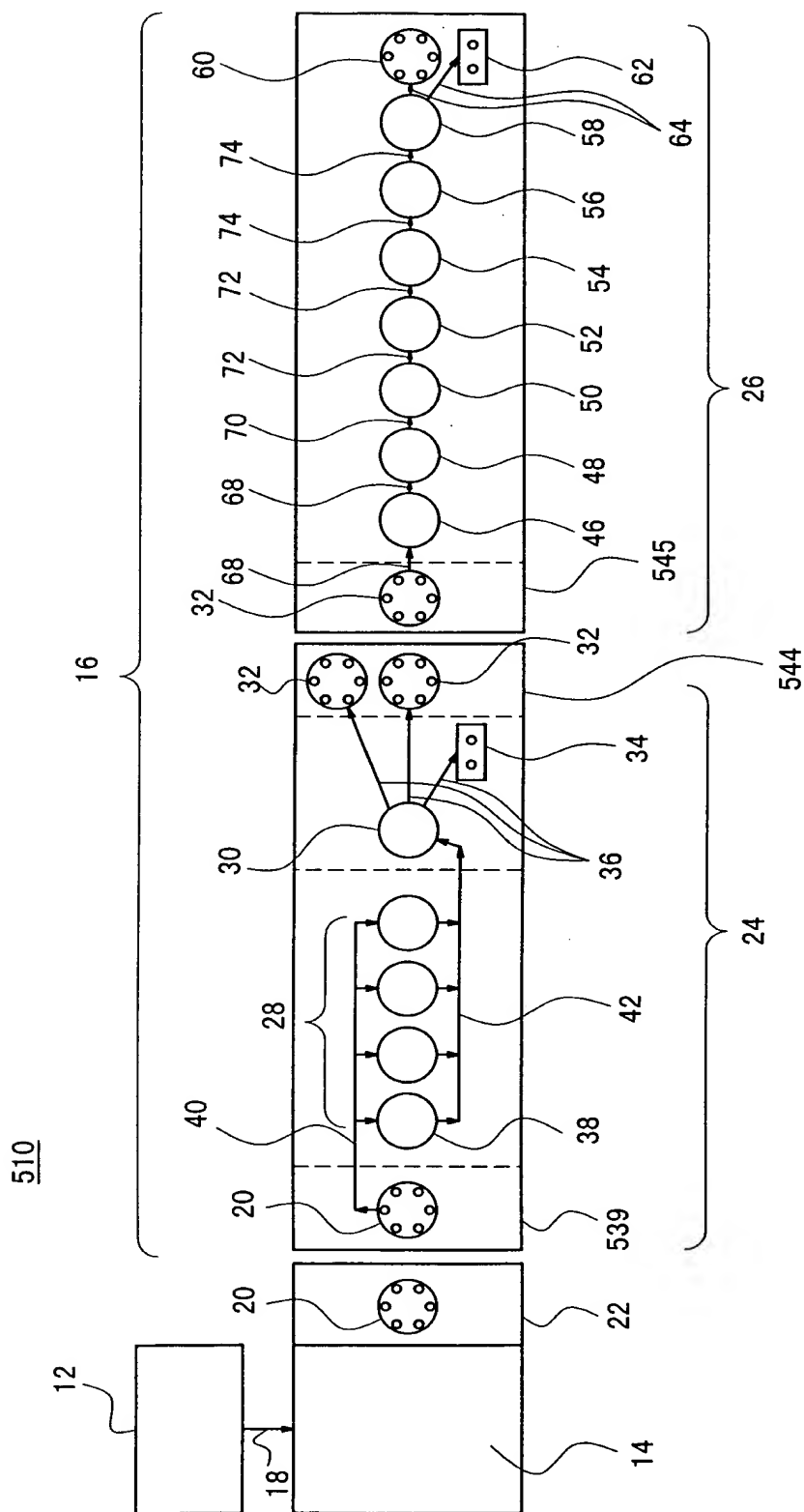


FIG. 16

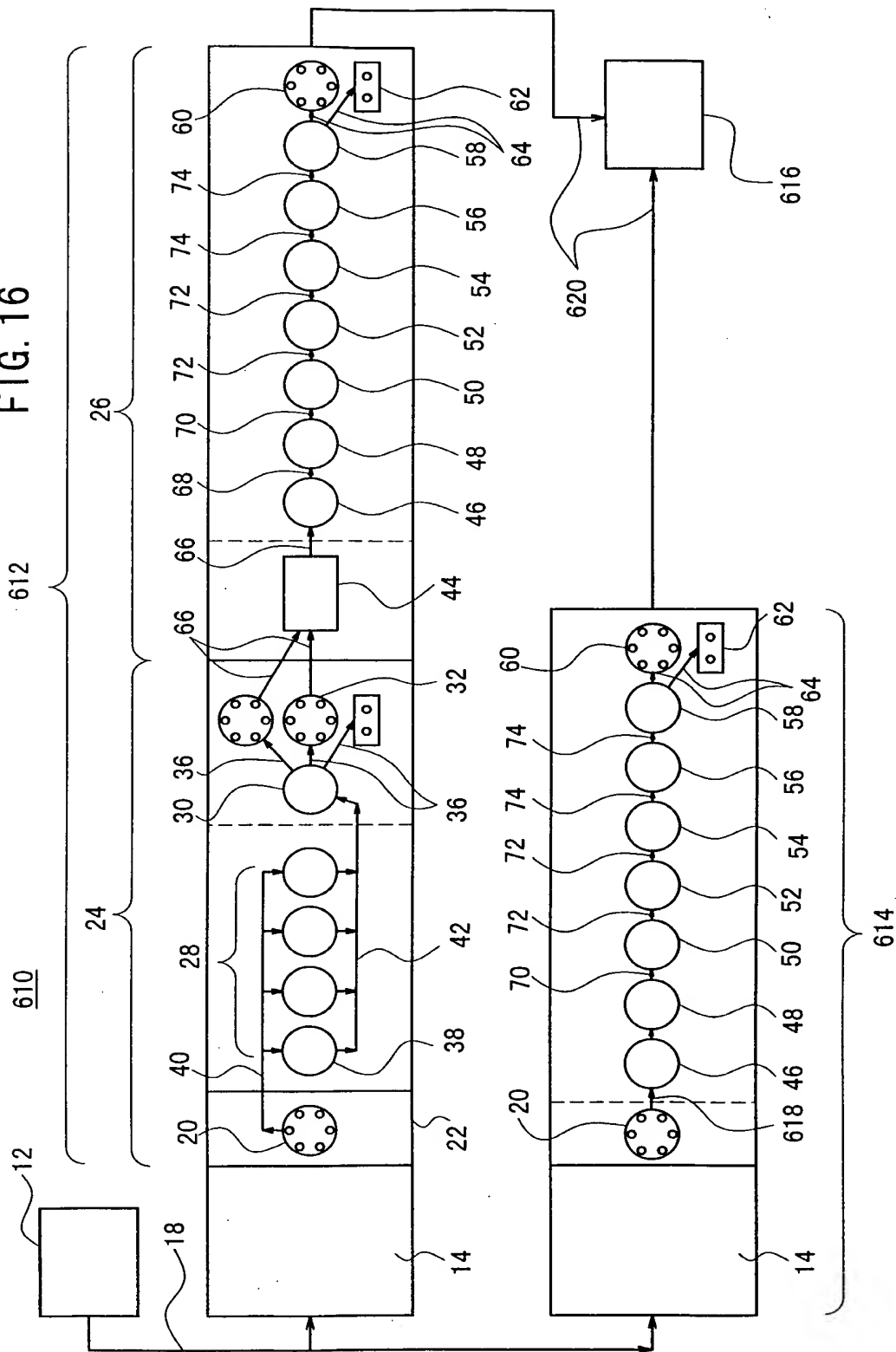


FIG. 17

